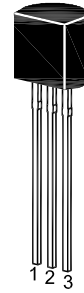


2SA608

PNP Silicon Epitaxial Planar Transistor

for low frequency and general purpose amplifier applications.

The transistor is subdivided into two groups F and G according to its DC current gain.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Collector Current (Pulse)	$-I_{CP}$	400	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$ at $-V_{CE} = 6\text{ V}$, $-I_C = 0.1\text{ mA}$	Current Gain Group F	h_{FE}	160	-	320	-
	Current Gain Group G	h_{FE}	280	-	560	-
	h_{FE}	70	-	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 40\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	0.3	V	
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{BE(sat)}$	-	-	1	V	
Transition Frequency at $-V_{CE} = 6\text{ V}$, $-I_C = 10\text{ mA}$	f_T	-	200	-	MHz	
Collector Output Capacitance at $-V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	4.5	-	pF	

